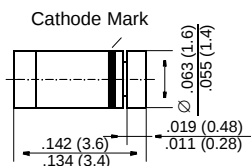


LL4151

Small Signal Diodes

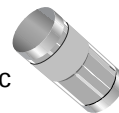
MiniMELF



Dimensions in inches and (millimeters)

FEATURES

- ◆ Silicon Epitaxial Planar Diode
- ◆ Fast switching diode in MiniMELF case especially suited for automatic insertion.
- ◆ This diode is also available in other case styles including the DO-35 case with the type designation 1N4151 and the SOD-123 case with the type designation 1N4151W.



MECHANICAL DATA

Case: MiniMELF Glass Case (SOD-80)

Weight: approx. 0.05 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Reverse Voltage	V_R	50	V
Peak Reverse Voltage	V_{RM}	75	V
Forward DC current at $T_{amb} = 25\text{ °C}$	I_F	200 ¹⁾	mA
Rectified Current (Average) Half Wave Rectification with Resist. Load at $T_{amb} = 25\text{ °C}$ and $f \geq 50\text{ Hz}$	I_O	150 ¹⁾	mA
Surge Forward Current at $t < 1\text{ s}$ and $T_j = 25\text{ °C}$	I_{FSM}	500	mA
Power Dissipation at $T_{amb} = 25\text{ °C}$	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	175	°C
Storage Temperature Range	T_S	-65 to +175	°C
¹⁾ Valid provided that electrodes are kept at ambient temperature.			

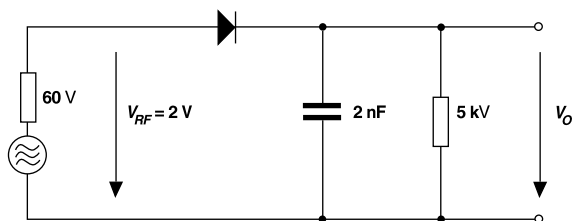
LL4151

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = \text{mA}$	V_F	—	—	1	V
Leakage Current at $V_R = 50 \text{ V}$ at $V_R = 50 \text{ V}$, $T_j = 150 \text{ }^\circ\text{C}$	I_R I_R	— —	— —	50 50	nA μA
Capacitance at $V_F = V_R = 0$	C_{tot}	—	—	2	pF
Reverse Recovery Time from $I_F = 10 \text{ mA}$ through $I_R = 10 \text{ mA}$ to $I_R = 1 \text{ mA}$ from $I_F = 10 \text{ mA}$ to $I_R = 1 \text{ mA}$, $V_R = 6 \text{ V}$, $R_L = 100 \text{ }\Omega$	t_{rr} t_{rr}	— —	— —	4 2	ns ns
Thermal Resistance Junction to Ambient Air	R_{thJA}	—	—	0.35 ¹⁾	K/mW
Rectification Efficiency at $f = 100 \text{ MHz}$, $V_{RF} = 2 \text{ V}$	η_v	0.45	—	—	—

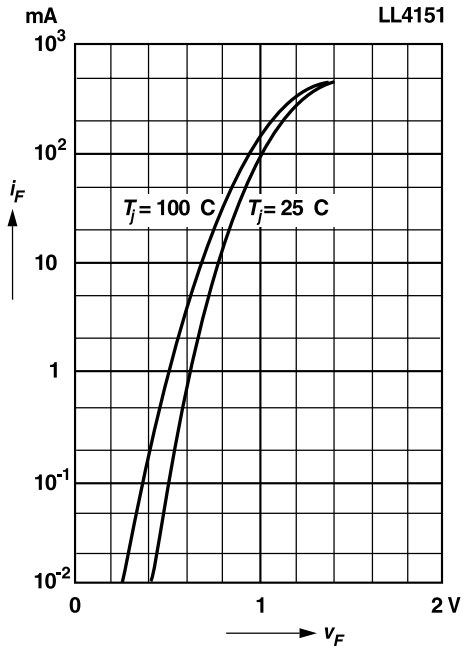
¹⁾ Valid provided that electrodes are kept at ambient temperature.



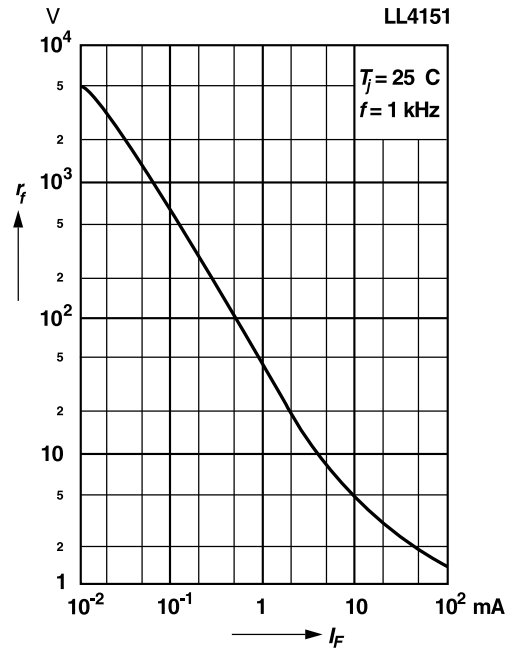
Rectification Efficiency Measurement Circuit

RATINGS AND CHARACTERISTIC CURVES LL4151

Forward characteristics

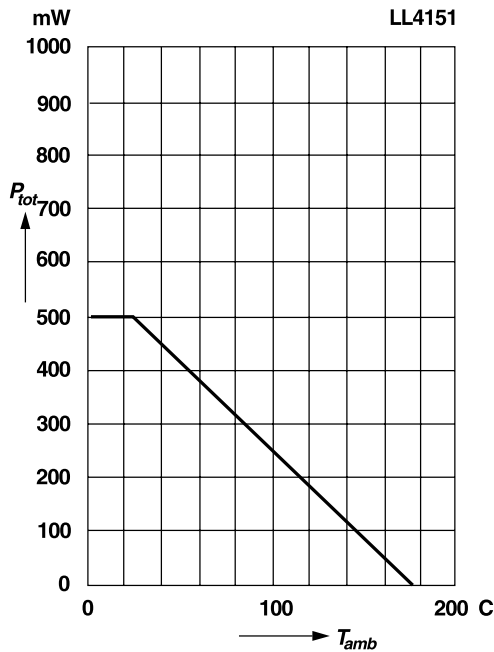


Dynamic forward resistance versus forward current

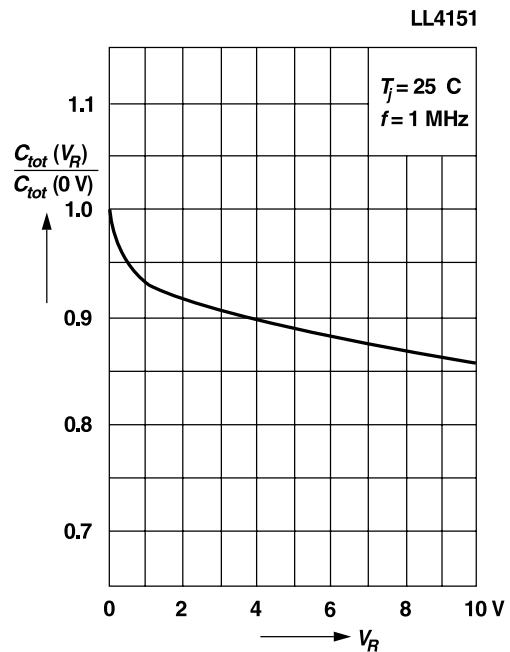


Admissible power dissipation versus ambient temperature

Valid provided that electrodes are kept at ambient temperature

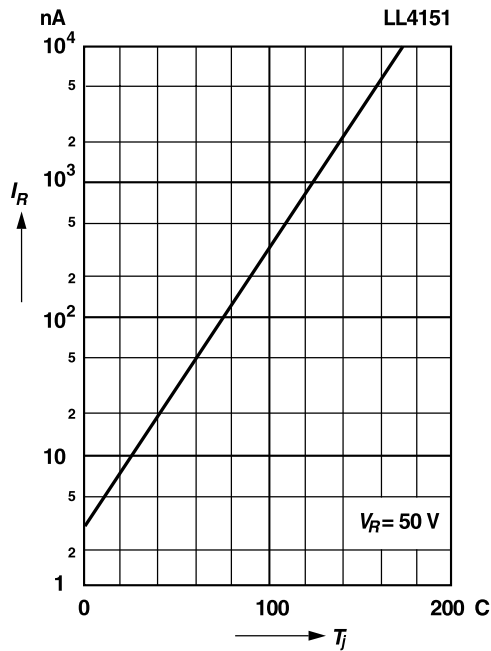


Relative capacitance versus reverse voltage



RATINGS AND CHARACTERISTIC CURVES LL4151

Leakage current
versus junction temperature



Admissible repetitive peak forward current versus pulse duration

Valid provided that electrodes are kept at ambient temperature

